

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

CR3-010GPP SERIES

GLASS PASSIVATED JUNCTION
GENERAL PURPOSE SILICON RECTIFIER
3.0 AMP, 50 THRU 1000 VOLTS

JEDEC DO-201AD CASE

FEATURES:

- 3.0 Amps at $T_A=75^\circ\text{C}$, 3/8" Lead Length
- Glass Passivated Chip
- Compression molded Epoxy
- Superior Solvent Resistance
- 200 Amps Surge Current
- Reliable Internal Construction
- Extensive Temperature Range

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 1N4001GPP Series types are 3.0 Amp Glass Passivated Junction Silicon Rectifiers which are high quality, well constructed, highly reliable components designed for use in all types of military, commercial, industrial, entertainment, computer, and automotive applications. **THIS DEVICE IS MANUFACTURED WITH A GLASS PASSIVATED CHIP FOR OPTIMUM RELIABILITY.**

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL	CR3-005GPP	CR3-010GPP	CR3-020GPP	CR3-040GPP	CR3-060GPP	CR3-080GPP	CR3-100GPP	UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
DC Blocking Voltage	V_R	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	280	420	560	700	V
Average Forward Current @ $T_A=75^\circ\text{C}$	I_O				3.0				A
Peak Forward Surge Current	I_{FSM}				200				A
Operating and Storage Junction Temperature	T_J, T_{stg}				-65 to +175				$^\circ\text{C}$
Thermal Resistance	Θ_{JA}				20				$^\circ\text{C/W}$

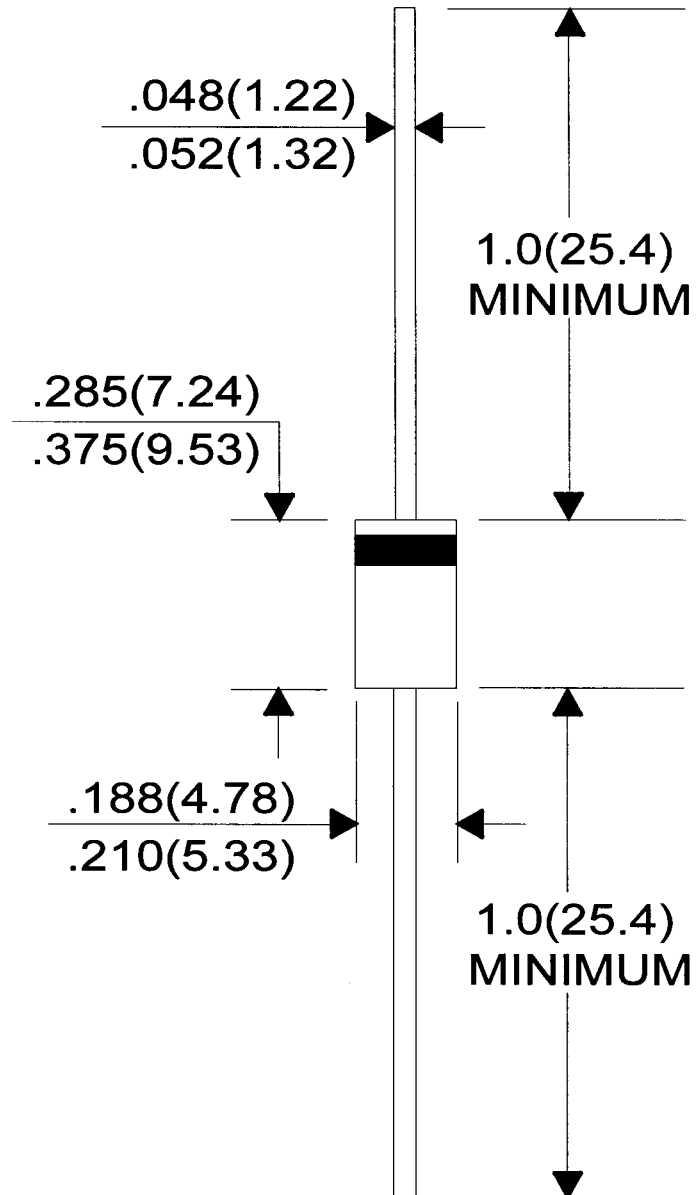
ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
V_F	$I_F=3.0\text{A}$			1.1	V
I_R	$V_R=\text{Rated } V_{RRM}$			5.0	μA
I_R	$V_R=\text{Rated } V_{RRM}, T_A=100^\circ\text{C}$			100	μA
C_J	$V_R=4.0\text{V}, f=1.0\text{MHz}$		30		pF

(SEE REVERSE FOR MECHANICAL OUTLINE)



JEDEC DO-201AD CASE - MECHANICAL OUTLINE



All Dimension in Inches (mm).